Minimum Inductance Calculation LIGO-T060247-00-C R. Abbott, Caltech 16 October, 2006

- A derivation is presented for the minimum inductor value, consistent with a lower boundary signal to noise ratio, for a series resonant RFPD read-out circuit.
 L Figure 1 shows a simplified schemetic of a series read out tapalogy.
 - 1.1. Figure 1 shows a simplified schematic of a series read-out topology

Figure 1



The photodetector equivalent parameters are in the boxed region. The output voltage, V_{out} , represents the input to a low-noise RF amplifier.

 C_d is the junction capacitance of the photo-diode. The photo-diode is assumed to be reverse-biased such that the internal diode can be neglected.

 R_d is the series resistance of the photo-diode. Any series resistance in the external resonant components can be considered to be added to R_d in this model.

1.2. Assuming L and C are driven at their series resonant frequency ω , the magnitude of the current flowing through R_d can be shown to equal:

$$I_{Rd} = I_1 \cdot \sqrt{\frac{1}{1 + (\omega \cdot R_d \cdot C_d)^2}}$$

1.3. The component of I1 attributable to shot-noise is given by:

$$I_{shot} = \sqrt{2 \cdot e \cdot I_{dc}}$$

Where I_{dc} is the photo-current flowing in the detector and e is is the electron charge (1.6 e -19 coulombs)

1.4. The output voltage due to shot-noise is given by:

$$Vout_{shot} = \omega \cdot L \cdot \sqrt{\frac{2 \cdot e \cdot I_{dc}}{1 + (\omega \cdot R_d \cdot C_d)^2}}$$

1.5. If $Vout_{shot}$ is to be a factor of N greater than the electronic noise E_n of the RF amplifier stage, a lower limit on L is given by:

$$L \ge \frac{N \cdot E_n}{\omega \cdot \sqrt{\frac{2 \cdot e \cdot I_{dc}}{1 + (\omega \cdot R_d \cdot C_d)^2}}}$$

1.6. Example calculation:

N = 5En = 1nV/ \sqrt{Hz} $\omega = 2 \cdot \pi \cdot 100$ MHz $I_{dc} = 50$ mA $R_{d} = 10 \Omega$ $C_{d} = 100$ pF

Calculated L $\geq 74~nH$